

Thermoreflectance-Based Submicron Temperature Profiling and Structure Function Analysis for Multilayer Nanostructures

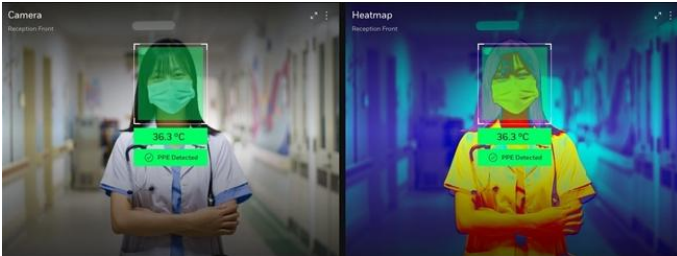
The 19th Korea-U.S. Forum on Nanotechnology

2025. 07. 04

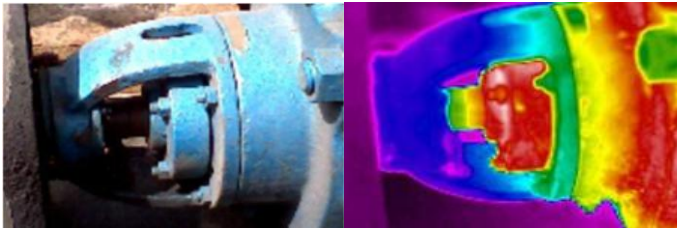
Presenter: Guesuk Lee

Analysis Using Thermal Imaging Measurement Technology

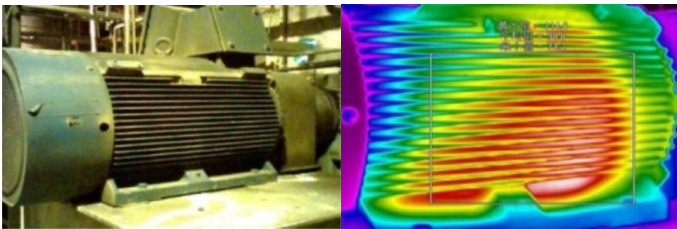
■ Various Analysis Using Temp. Measures



Covid-19 Fever
Screening

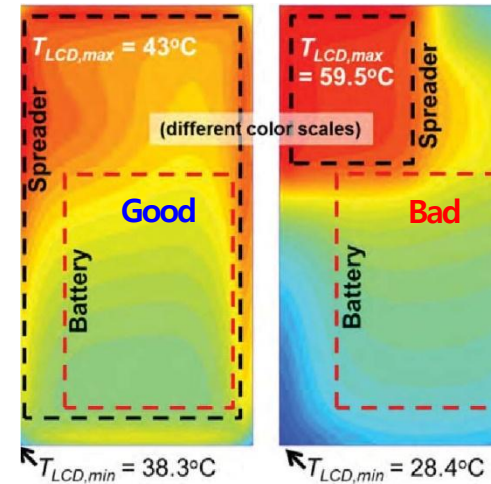


Internal Bearing



Internal Motor

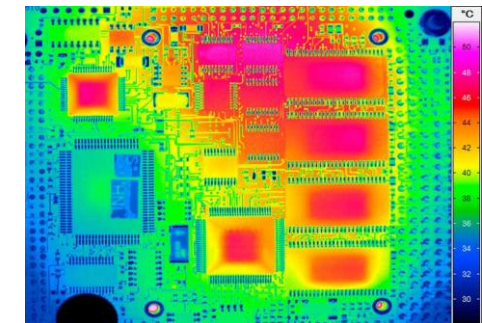
■ Analysis in the Electronics Field



(15, Engineering, Smart Phone Thermal Management)

Thermal Distribution
Optimization Design

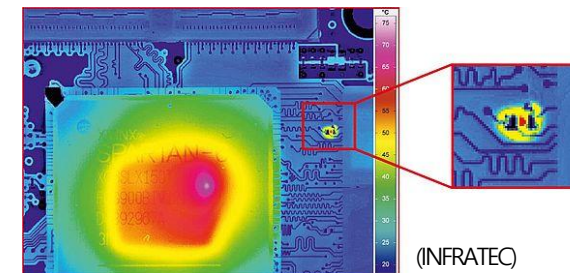
Improper Layout
Improper Thermal Spreader
...



(INFRATEC)

Defect Analysis

Short Circuit
Incorrect Location (Assembly)
Insufficient Tin for Soldering
...



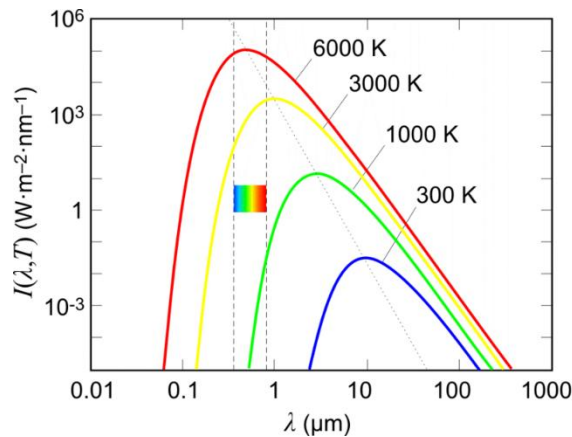
(INFRATEC)

Thermal imaging measurement featuring advantages such as **2D analysis (location)**, **non-contact**, and **real-time monitoring**

Thermal Analysis Using Infrared Measurement

■ Planck's Law(Germany, 1900) & Infrared (IR) Cam.

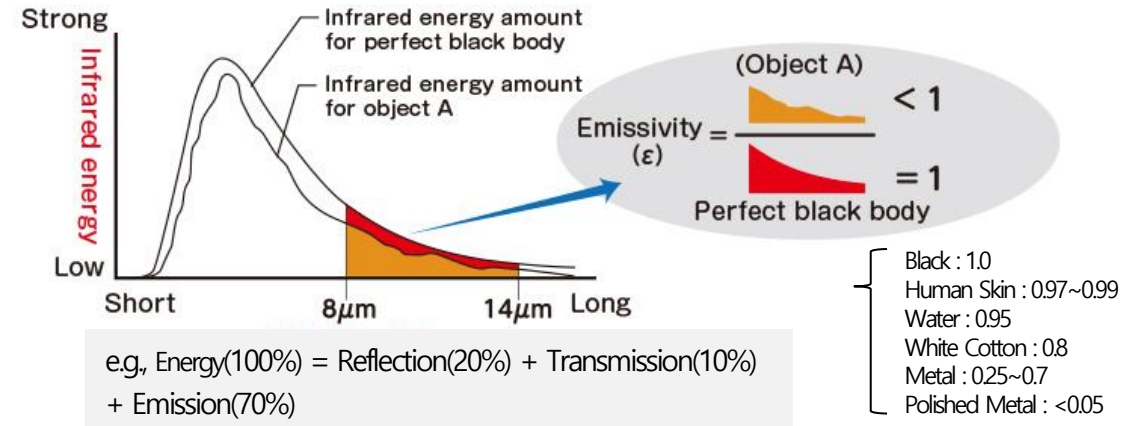
- All objects above absolute zero emit thermal radiation (energy).
- The intensity of thermal radiation is related to 1) Object Temperature, and 2) Emissivity (Surface Condition).
- Photodetector (light-to-electricity conversion, e.g., photodiode) + Image Sensor (image processing, e.g., CCD, CMOS)



Radiation Energy According to Temperature



Visually Observable Radiant Energy



Infrared Energy Emission Based on Emissivity



Same Temp. Diff. Emissivity Same Temp. Diff. Reflectivity Processing for Temp. Measurement

Infrared Measurement Results by Emissivity

IR cameras measure the amount of infrared radiation energy emitted from objects, not temperature itself

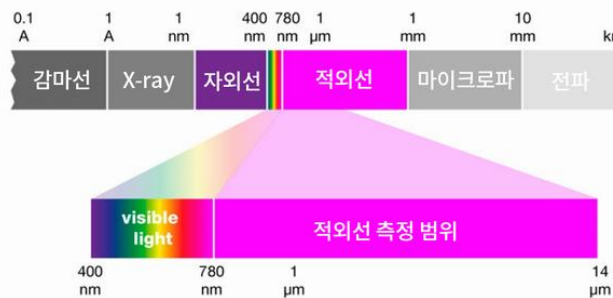
Thermal Image Measurement & Spatial Resolution

■ Spatial Resolution

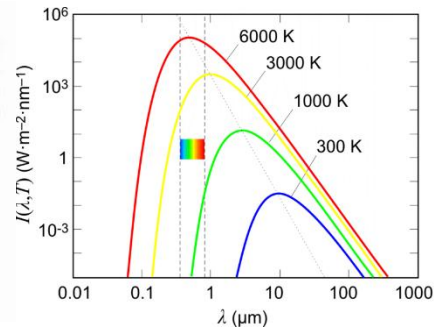
- Abbe (Netherlands 1873) revealed **the limit of resolution**.
- **To improve resolution**, the wavelength must be shortened.

$$\downarrow d = \frac{\lambda}{2n\sin\theta} \quad \downarrow$$

d : Resolution
 $n\sin\theta$: Numerical Aperture (NA), max = 1
 n : Refractive index
 λ : Wavelength of light



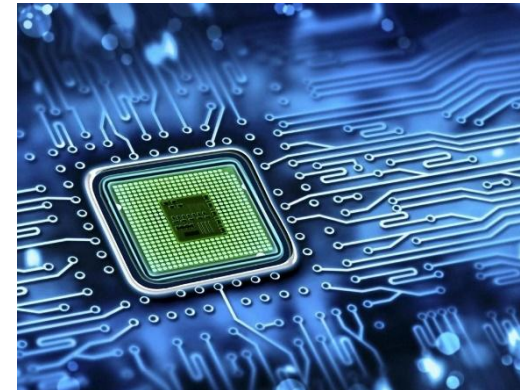
Theoretical Resolution Limit: **0.36μm ~ 7μm**



Resolution Limit in 300K: **5μm**

■ Thermal Reliability Issues in Integrated Circuits

- Smaller Features (10nm~100μm) → Contact is Not Possible.
- Increasing Power Density → **Higher Heat** / **Localized Heat**
- Lifetime : $15^\circ\text{C} \uparrow \rightarrow$ **Lifetime 1/4 ↓**
- High Speed Response

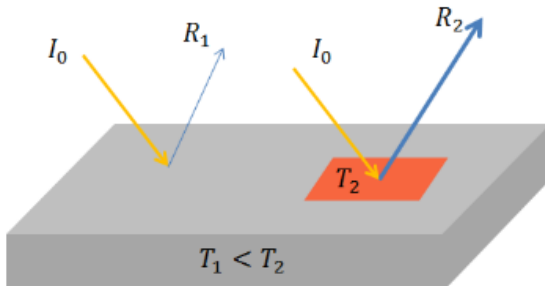


IR thermal imaging **lacks sufficient resolution** for dense circuit inspection in the submicron range.

Thermo-Reflectance Measurement Equipment – Spatial/Temp. Resolution

■ Principle of Thermo-Reflectance Measurement (ref, MicrosanJ / Nanoscopyesystems / ALTER Tech. / Electronics Cooling)

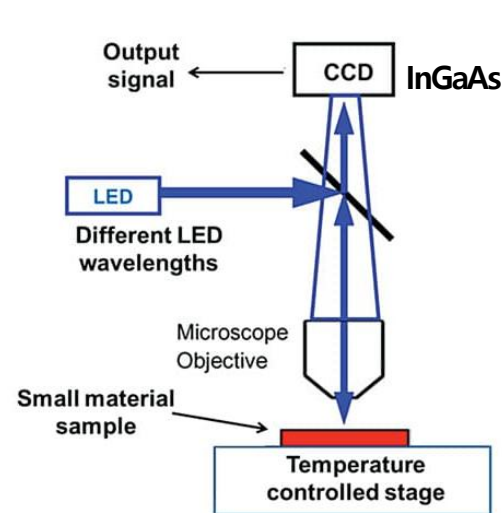
- The optical reflectance (R) of a sample changes depending on its temperature. (1968, Thermoreflectance in Semiconductors, Phys. Rev.)
- By measuring the change in reflectance (ΔR), we can experimentally determine the temperature change (ΔT) \rightarrow requires the TR coefficient (C_{TR})
- When CTR is large at a specific illumination wavelength, temperature resolution improves \rightarrow Proper illumination wavelength selection is required



$$\frac{\Delta R}{R} = \left(\frac{1}{R} \frac{\partial R}{\partial T} \right) \Delta T = C_{TR} \Delta T$$

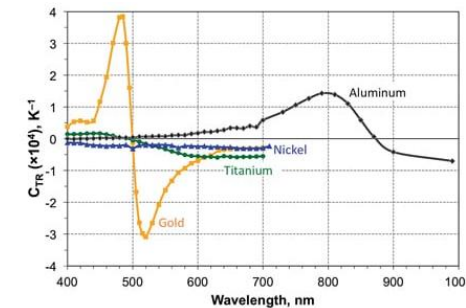
C_{TR} : Thermoreflectance Coefficient ($10^{-2}/K \sim 10^{-5}/K$)

$C_{TR} = f(\text{Ambient Temperature, Illumination Wavelength [Visible LED Source], Material \& Surface Prop. [Polishing, etc.], Optics/Microscope NI})$



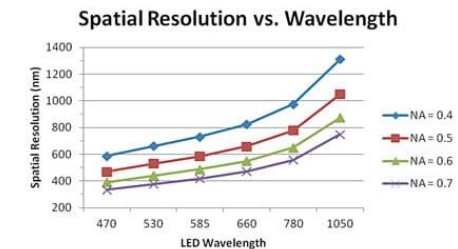
Measurement Process of Reflectance Coefficient @ Target Temperature Range

Material-specific Thermoreflectance Coefficient & Illumination Wavelengths



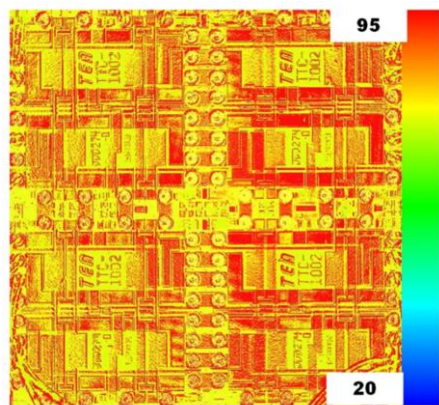
Material	Illumination Wavelength					
	365 nm (UV)	470 nm (Blue)	530 nm (Green)	585 nm (Yellow)	660 nm (Red)	780 nm (N-IR)
Gold (Au)		■	■			
Aluminum (Al)						■
Nickel (Ni)				■	■	
Titanium (Ti)				■	■	
Silicon (Si)		■				
Gallium Arsenide (GaAs)		■				
Gallium Nitride (GaN)	■	■	■			
Indium Phosphide (InP)		■				
Thru-the-Substrate Imaging						■

Optical System and Resolution

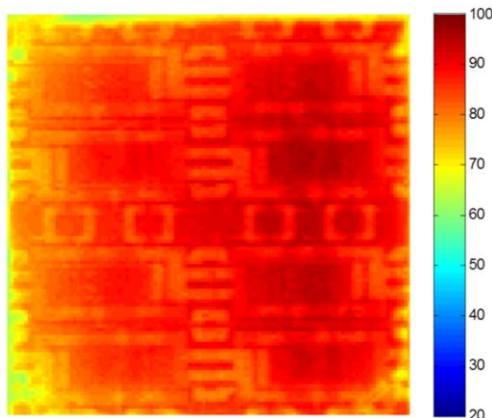


Comparison of Thermal 2D Images

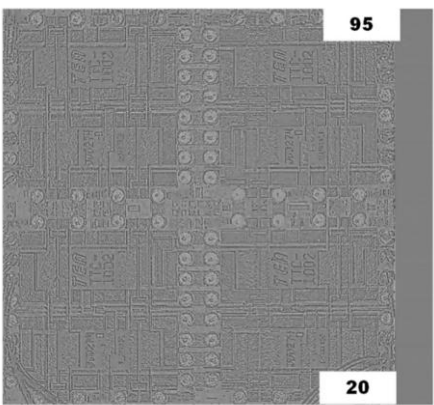
■ TR(Visible Light) vs. Thermal Emission(IR) vs. Optical



Thermoreflectance



Infrared



Microscope

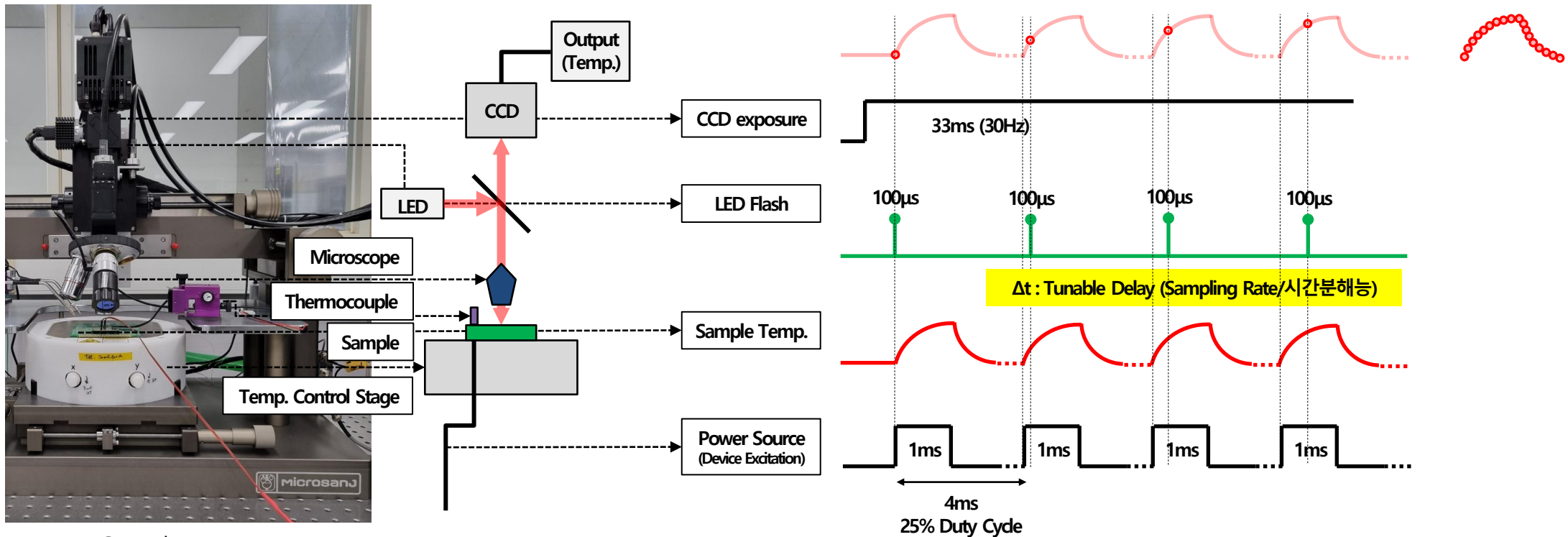
Principle	Change in reflectance by Temp.	Radiation Emissivity by Temp.	-
Coefficient	Reflectance coefficient by material	Emissivity by material	-
Spatial Resolution	0.35 ~ 0.85μm	3.0 ~ 10.0μm	0.2μm
Temp. Resolution	0.08K (Thermoreflectance Sensitivity)	0.02K (Radiative energy sensitivity)	-
Others	AC Technique W/ Lock-in	Si transparent to IR Metals are poor emitters.	-

The spatial resolution of thermo-reflectance measurement using visible light is about 10 times higher than that of IR.

Transient Thermo-Reflectance Measurement Equipment – Temporal Resolution

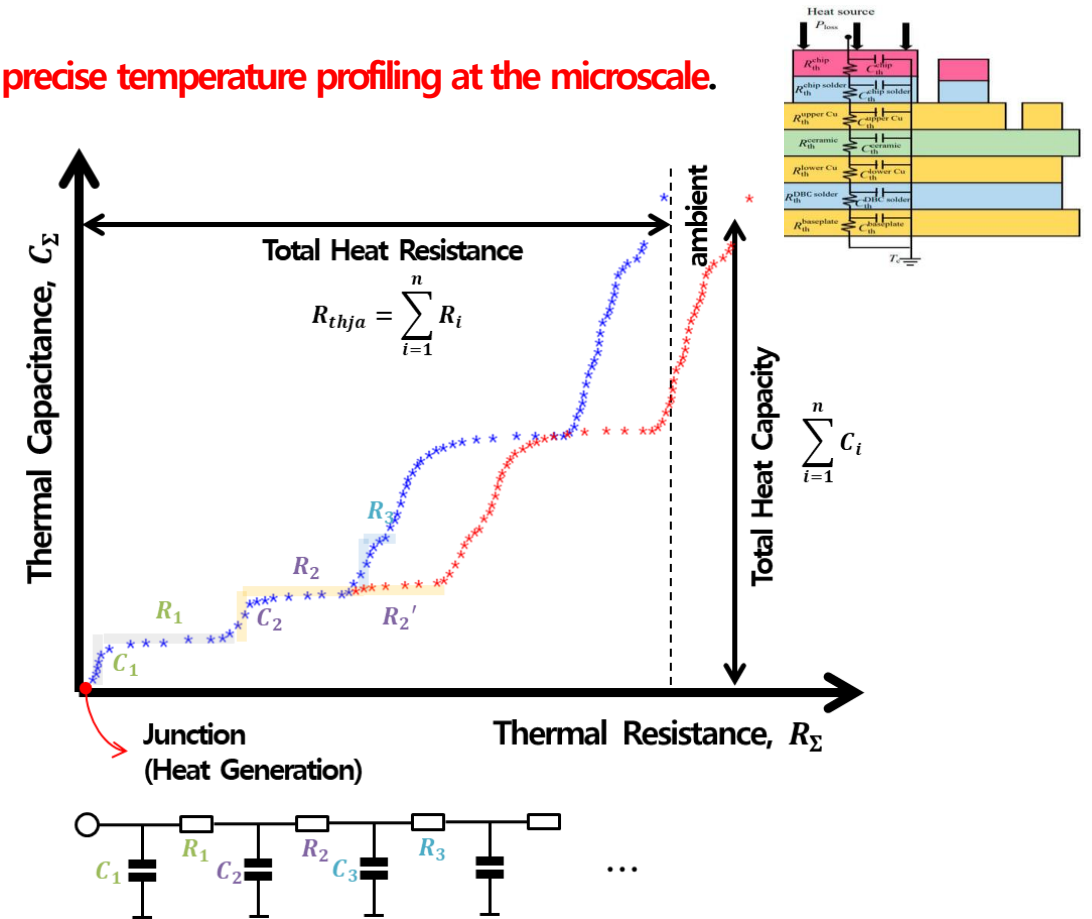
■ Transient Measurement Based on Lock-in Cycle

- Lock-in : In noisy environments, extracts Amplitude and Phase signals using a Low-Pass Filter



Transient characteristics can be measured through LED Flash Delay

- **Structure function analysis** requires thermal transient response – demanding **precise temperature profiling at the microscale**.



7

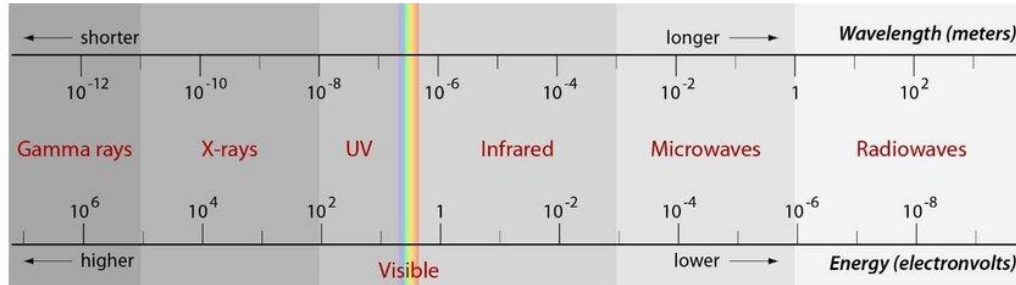
Thank You

gslee@keti.re.kr

(참고) UV 기반 열 이미지 측정?

Electromagnetic Spectrum

출처: 105281/zenodo.3534245



Method	Wavelength[nm]	Application	
Infrared	700-10 ⁵	IR cam	3 μ m
Visible	400-700	TTR 광학	300nm 200nm
UV	1-400	EUV	13.5nm
X-rays	0.01-1	SEM(주사) TEM(투과)	5Å 1Å
Gamma Rays	<0.01	암치료	

* Si 원자 공유반경 : 1.11Å = 0.111nm

→ 재료 손상 위험
→ 온도에 대한 계수 X

Fluorescent(형광) Micro-thermography

· 형광체 코팅 → 자외선 조사 → 적외선 검출 온도 측정

